BATOP optoelectronics

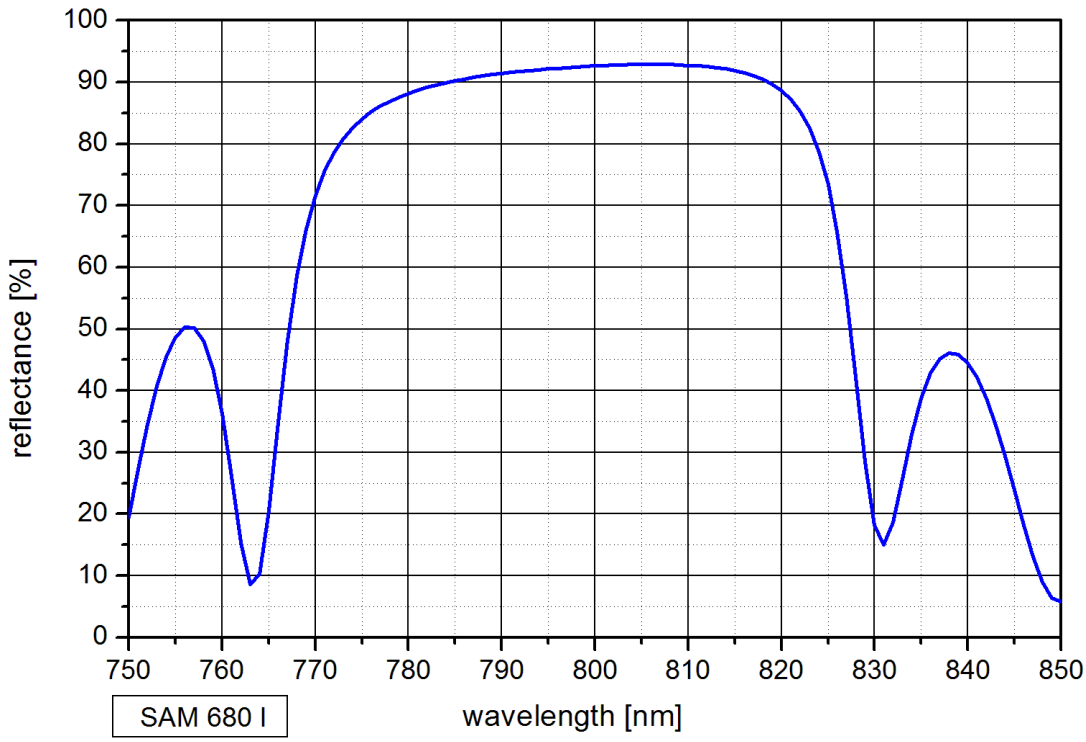
SAM™ data sheet SAM-800-7-1ps-x, λ = 800 nm

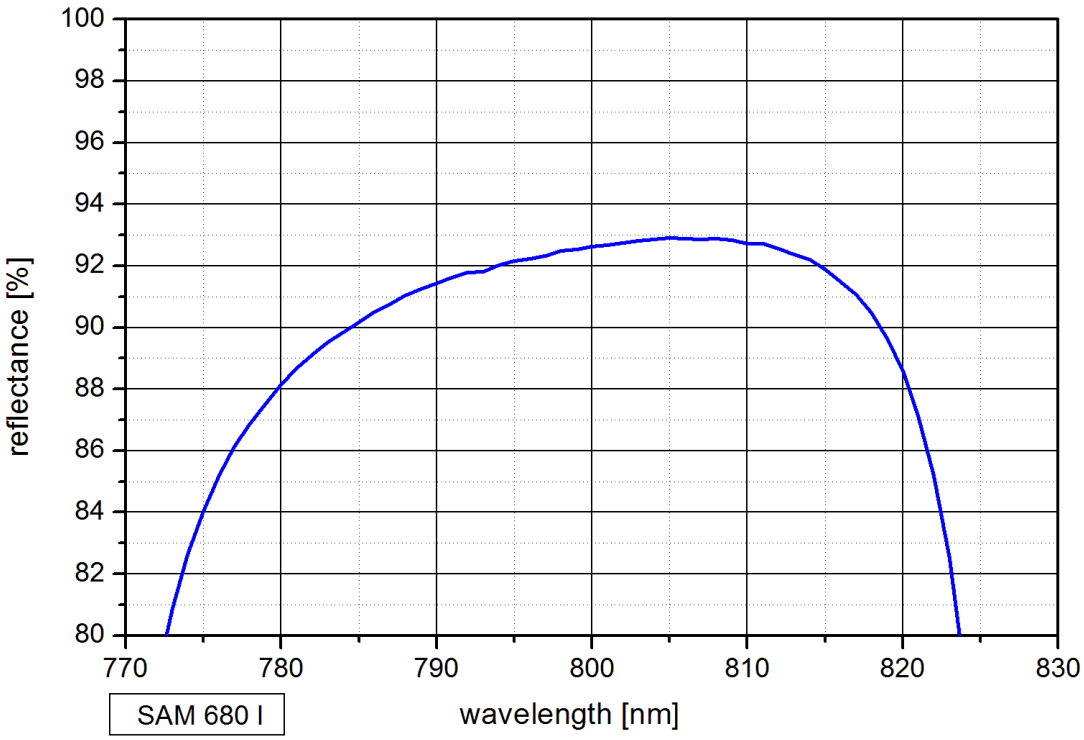
Laser wavelength	λ = 800 nm
High reflection band	λ = 780 .. 820 nm
Absorbance	A_0 = 7 %
Modulation depth	ΔR = 4 %
Non-saturable loss	A_{ns} = 3 %
Saturation fluence	Φ_{sat} = 70 µJ/cm^2
Relaxation time constant	τ ~ 1 ps
Damage threshold	Φ = 2 mJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm
Protection	the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm ∅
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm ∅
x = 25.0 w	soldered on a water cooled Cu-cylinder with 25.0 mm ∅
x = FC	mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance




100
98
96
94
92
90
88
86
84
82
80
reflectance [%]
770
780
790
800
810
820
830
wavelength [nm]
SAM 680 I